Gallium–Indium–Zinc-Oxide-Based Thin-Film Transistors: Influence of the Source/Drain Material

Pedro Barquinha, Anna M. Vilà, Gonçalo Gonçalves, Luís Pereira, Rodrigo Martins, Joan R. Morante, and Elvira Fortunato

Abstract—During the last years, oxide semiconductors have shown that they will have a key role in the future of electronics. In fact, several research groups have already presented working devices with remarkable electrical and optical properties based on these materials, mainly thin-film transistors (TFTs). Most of these TFTs use indium–tin oxide (ITO) as the material for source/drain electrodes. This paper focuses on the investigation of different materials to replace ITO in inverted-staggered TFTs based on gallium–indium–zinc oxide (GIZO) semiconductor. The analyzed electrode materials were indium–zinc oxide, Ti, Al, Mo, and Ti/Au, with each of these materials used in two different kinds of devices: one was annealed after GIZO channel deposition but prior to source/drain deposition, and the other was annealed at the end of device production. The results show an improvement on the electrical properties when the annealing is performed at the end (for instance, with Ti/Au electrodes, mobility rises from 19 to 25 cm$^2$/V·s, and turn-on voltage drops from 4 to 2 V). Using time-of-flight secondary ion mass spectrometry (TOF-SIMS), we could confirm that some diffusion exists in the source/drain electrodes/semiconductor interface, which is in close agreement with the obtained electrical properties. In addition to TOF-SIMS results for relevant elements, electrical characterization is presented for each kind of device, including the extraction of source/drain series resistances and TFT intrinsic parameters, such as $\mu_i$ (intrinsic mobility) and $V_{T1}$ (intrinsic threshold voltage).

I. INTRODUCTION

The THIN-FILM transistor (TFT) industry is still tightly connected to the silicon technology, and it will most likely remain that way during the next years. However, new research areas have been opened with the appearance of the first semiconductor oxide-based transistors in 1996 by Prins et al. [1]. At that time, little attention was given to the semiconductor material (Sb-doped SnO$_2$), but in 2003–2004, the “big boom” happened with the presentation of several oxide semiconductor TFTs based on ZnO [2]–[5] or ZnO compound materials [6] with remarkable electrical properties, which are comparable to or even better than amorphous silicon (a-Si) TFTs. Once these devices were reported, several ideas appeared concerning their application, with the main driving force related to the next generation of flexible and transparent devices processed at low temperatures, namely for display applications. In fact, from that time until today, several reports have been presented concerning (fully) transparent transistors with reduced processing temperatures and/or enhanced electrical properties in comparison with the first ZnO TFTs [7]–[9]. The key point that allowed this evolution was the exploitation of new multicomponent oxide semiconductors based on heavy-metal cations, e.g., zinc–tin oxide (ZTO) [8], indium–zinc oxide (IZO) [7], [9], [10], and gallium–indium–zinc oxide (GIZO) [11], which have excellent electrical properties in spite of their amorphous structure, something that is unusual for conventional covalent semiconductors [10].

II. EXPERIMENTAL DETAILS

The TFTs were produced using heavily doped ($N_A \approx 10^{17}$ cm$^{-3}$) p-type silicon substrates (2.5 $\times$ 2.5 cm) coated with 100-nm-thick thermally grown SiO$_2$, which acted as the gate dielectric. Si was simultaneously used as the substrate and the common gate of the devices. A Ti (15 nm)/Au (135 nm) film was deposited by electron beam (e-beam) evaporation on the backside of Si (after etching the backside SiO$_2$ with a buffered HF solution) to form the gate electrode.

Manuscript received August 9, 2007; revised December 12, 2007. This work was supported in part by the European Commission under Contract NMP3-CT-2006-032231 and in part by the Portuguese Science and Technology Foundation (FCT), Ministry for Science, Technology, and Higher Education (MCTES), under Projects POCI/CTM/55945 and POCI/CTM/55942. The works of P. Barquinha and G. Gonçalves were supported by FCT-MCTES under Fellowships SFRH/BD/17970/2004 and SFRH/BD/27313/2006, respectively. The review of this paper was arranged by Editor M. Anwar.

Pedro Barquinha, Anna M. Vilà, Gonçalo Gonçalves, Luís Pereira, Rodrigo Martins, Joan R. Morante, and Elvira Fortunato are with the Materials Science Department, Materials Research Center/Institute of Nanotechnologies, Nanomaterials and Nanosciences (CENIMAT/3N) and Center of Excellence in Microelectronics Optoelectronics and Processes/Instituto de Desenvolvimento de Novas Tecnologias (CEMOP/UNINOV), Faculty of Sciences and Technology, New University of Lisbon, 2829-516 Caparica, Portugal (e-mail: pmce@fct.unl.pt).

A. M. Vilà and J. R. Morante are with the Department of Electronics, Faculty of Physics, University of Barcelona, 08007 Barcelona, Spain.

Digital Object Identifier 10.1109/TED.2008.916717

954 IEEE TRANSACTIONS ON ELECTRON DEVICES, VOL. 55, NO. 4, APRIL 2008

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A 50-nm-thick GIZO layer (the semiconductor) was then deposited by RF magnetron sputtering at room temperature in a Pfeiffer Vacuum Classic 500 system. A 3-in-diameter ceramic target from LTS was used at 15 cm from the substrate, at a base pressure of $5 \times 10^{-4}$ Pa, an oxygen partial pressure of $4 \times 10^{-2}$ Pa, a processing pressure ($\text{Ar} + \text{O}_2$) of $7 \times 10^{-1}$ Pa, and an RF power of 75 W. Different source/drain electrodes—Ti, Al, Mo, and Ti/Au, all 200 nm thick—were e-beam evaporated at a rate of 2 A/s on top of GIZO to evaluate the influence of the various electrode materials on the electrical properties of the TFTs. In addition to these metals, IZO (200 nm) deposited by RF magnetron sputtering was also tested as a source/drain electrode material. The details concerning IZO can be found elsewhere [7]. Both the semiconductor and the source/drain layers were patterned by liftoff, and the produced transistors had a fixed width $W$ of 50 $\mu$m, whereas the length $L$ was changed between 50 and 5 $\mu$m. Two different kinds of transistors were produced with each source/drain material: one (TFT A) was annealed after GIZO but prior to source/drain deposition; the other (TFT B) was annealed at the end of device production. Annealing was performed in a Barnstead Thermolyne F21130 tubular furnace, with a constant flow of nitrogen, at 250 °C for 1 h.

III. RESULTS AND DISCUSSION

Fig. 1 shows the transfer and output characteristics of GIZO-based TFTs with Ti/Au source/drain electrodes, which are annealed at two different processing stages—before (TFT A) and after (TFT B) source/drain deposition. The data reveal a general improvement on the electrical properties of device B, as traduced by an enhancement on the maximum $I_{DS}$, i.e., $I_{DS_{\text{max}}}$ (0.08 against 0.05 mA), and the field-effect mobility $\mu_{FE}$ (24.5 against 18.8 cm²/V·s, as calculated by the transconductance with $V_{DS} = 1$ V) and a slightly lower threshold voltage $V_T$ (12.8 against 14.6 V). The on/off ratio remained essentially the same, i.e., around $6 \times 10^7$. This enhancement could be related to some changes in the interface between the source/drain and the semiconductor, such as a decrease of the barrier associated with the contact of materials with different workfunctions [19]. Indeed, by the results obtained using time-of-flight secondary ion mass spectrometry (TOF-SIMS) (Fig. 2), one can clearly see that TFT B data reveal a broader intersection between Au and Ti (the two metals that compose the source/drain electrodes and that obviously have an influence on the contact’s electrical performance, where Ti is the adhesion layer) and Ti and GIZO than for TFT A. These broad intersections are related...
to the diffusion of the constituent materials and, thus, with the formation of transition regions between the electrodes and the semiconductor that should improve the electrical characteristics. This evolution of properties from device A to B is more drastic with Ti or Ti/Au electrodes and barely noticeable with Mo electrodes. From all the tested source/drain materials, IZO is the one that presents fewer changes from A to B, presumably because it should be very similar to GIZO in terms of structure.

In fact, TOF-SIMS data of TFT A and TFT B with GIZO/IZO is the one that presents fewer changes from A to B, presumably because it should be very similar to GIZO in terms of structure. This evolution of properties from device A to B is more drastic with Ti or Ti/Au electrodes and barely noticeable with Mo electrodes. From all the tested source/drain materials, IZO is the one that presents fewer changes from A to B, presumably because it should be very similar to GIZO in terms of structure.

A comparison between the various source/drain materials is shown in Fig. 3 for devices with $W/L = 50/50 \ \mu m$. The data show some differences on the transfer characteristics, mainly the turn-on voltage $V_{on}$, which is considerably more negative for Mo source/drain electrodes. This could be related to the results obtained by TOF-SIMS, where no clear evidence of interfacial layer was observed for Mo/GIZO. On the contrary, since an interfacial layer is formed when Ti (or Ti/Au) electrodes are used, presumably TiO$_x$ (note that Ti has a small free energy of oxidation), this could be pushing $V_{on}$ toward more positive values. We are currently working to experimentally clarify this point. Off-current variations can be attributed to device processing nonuniformity and measurement error, as revealed by the characterization of different devices processed under the same conditions in different runs.

The inset of Fig. 3 shows magnification of output characteristics, where it can be seen that Mo and Ti/Au allow higher $I_{DS\, max}$ than IZO and Ti source/drain electrodes. This suggests that the first two contacts have a higher efficiency of injection than the last two contacts. Note that for high $V_{DS}$ (when the TFT is getting closer to or is in the saturation mode), most of that voltage is dropped near the source (i.e., injecting contact) than near the drain [15], [17]. Thus, a highly efficient contact is necessary to attain good electrical properties. The previous statement obviously assumes that the contacts are associated with some resistances, as will be later explored.

The electrical properties of the TFTs with different source/drain electrodes are listed in Table I and are in agreement with the previous statements. In fact, mobility is higher for Ti/Au and Mo contacts, both in linear ($\mu_{FE}$) and saturation ($\mu_{sat}$) regimes. Note that $\mu_{sat}$ is always lower than $\mu_{FE}$, which can be attributed to the increased scattering effects in the channel due to the higher $V_{DS}$ used to determine $\mu_{sat}$. Concerning $V_T$ and on/off ratio, no significant differences are found between all the electrodes, with the obtained values around 12.5–13.7 V and $6 \times 10^7 - 2 \times 10^8$, respectively.

### Table I

<table>
<thead>
<tr>
<th>Source/Drain material</th>
<th>$\mu_{FE}$ (cm$^2$/V$\cdot$s)</th>
<th>$\mu_{sat}$ (cm$^2$/V$\cdot$s)</th>
<th>$V_{on}$ @ $V_{GS}=15$V</th>
<th>$V_{on}$ @ $V_{DS}=15$V</th>
<th>$V_{T}$ @ $V_{DS}=15$V</th>
</tr>
</thead>
<tbody>
<tr>
<td>IZO</td>
<td>20.7</td>
<td>15.7</td>
<td>2.1x10$^8$</td>
<td>1.0</td>
<td>12.7</td>
</tr>
<tr>
<td>Ti</td>
<td>21.1</td>
<td>16.9</td>
<td>1.3x10$^8$</td>
<td>2.0</td>
<td>13.7</td>
</tr>
<tr>
<td>Mo</td>
<td>22.6</td>
<td>17.4</td>
<td>6.0x10$^7$</td>
<td>-2.0</td>
<td>12.5</td>
</tr>
<tr>
<td>Ti/Au</td>
<td>24.5</td>
<td>18.7</td>
<td>6.1x10$^7$</td>
<td>2.0</td>
<td>12.9</td>
</tr>
</tbody>
</table>

To evaluate the performance of different materials, the contact resistance and intrinsic semiconductor parameters were studied. For a low $V_{DS}$, the total TFT-ON resistance $R_T$ can be written as [20]

$$ R_T = \frac{V_{DS}}{I_{DS}} = r_{ch}L + R_S + R_D $$

(1)

where $r_{ch}$ is the channel resistance per channel-length unit, and $R_S$ and $R_D$ are the series resistances associated with the source and drain, respectively. Using the basic transistor equation from the gradual channel approximation, $r_{ch}$ is given by [20]

$$ r_{ch} = \frac{L}{\mu_i C_{ox} W (V_{GS} - V_{T})} $$

(2)

where $\mu_i$ and $V_{T}$ are the intrinsic semiconductor mobility and threshold voltage, respectively, representing the conduction channel without the influence of the contact series resistance. The determination of these parameters involves the determination and plotting of $R_T$ (at low $V_{DS}$, i.e., in linear regime) for different $V_{GS}$ and $L$, then fitting the experimental values with linear curves for each $V_{GS}$ (Fig. 4). The intercept with the y-axis of each fitting gives $R_S + R_D$, whereas $r_{ch}$ is given by the slope, as evidenced by (1). Plotting the reciprocal of $r_{ch}$ as a function of $V_{GS}$ and fitting the results with a linear curve, $\mu_i$ (slope) and $V_{T}$ ($x$-axis interception) can be obtained according to (2).

The obtained intrinsic parameters are shown in Fig. 5, together with the evolution of $\mu_{FE}$ and $V_T$ with $L$. Concerning...
the intrinsic parameters, namely $\mu_i$ and $V_{T_i}$, no considerable changes were verified among the tested material, which is an expectable result since the model takes into account that part of the applied $V_{GS}$ is dropped by the source/drain contact resistances.

In all the devices, $\mu_{FE}$ follows the same trend as $L$, i.e., it decreases for small channel lengths. Two aspects are worth noticing here. 1) The $\mu_i$ values match quite well with the $\mu_{FE}$ values of devices with a long channel (50 $\mu$m); this means that, in this case, $R_S$ and $R_D$ should not be of significant influence. 2) As $L$ decreases, the relative influence of $R_S$ and $R_D$ in $R_T$ increases ($R_S$ and $R_D$ are independent of $L$, but the product $r_{ch} \times L$ decreases); thus, a larger voltage is dropped at the contact resistances for smaller $L$, thus lowering $\mu_{FE}$ [17]. In particular, this means that the real voltages (both $V_{DS}$ and $V_{GS}$) applied inside the device, after passing the electrodes, are diminished as $L$ decreases. This relative effect of the resistances is clearly seen in Fig. 6, where both $R_C = R_S + R_D$ and $r_{ch} \times L$ for various $L$ are plotted as a function of $V_{GS}$.

For all the materials, both $r_{ch} \times L$ and $R_C$ are $V_{GS}$ dependent, i.e., they decrease for larger $V_{GS}$. This can be justified by the increase of the carrier concentration as $V_{GS}$ increases, both in the channel (the field effect phenomenon) and outside the channel defined by the lithographic mask (i.e., outside the space defined by $L$), since source/drain to gate overlaps exist [13], [14]. In the present case, since the gate electrode covers all the substrate, this overlap is maximized.

As shown in Fig. 6, as $L$ increases, the contribution of $R_C$ to $R_T$ decreases, agreeing quite well with the data depicted in Fig. 5. For instance, if long and short devices ($L = 50$ and 5 $\mu$m) are considered, different evolutions of $\mu_{FE}$ are observed:

For $L = 50 \mu$m, since the $R_C$ contribution to $R_T$ is negligible throughout the range of the studied $V_{GS}$, $\mu_{FE}$ will mostly depend on $r_{ch}$, which is low for devices where the source/drain electrodes are based on Ti/Au and Mo and high for those based on IZO and Ti. Thus, $\mu_{FE}$ increases in the following order of the materials used for the source/drain electrodes, i.e., IZO, Ti, Mo, and Ti/Au, as shown in Table I. Now, even if one does not calculate the peak value of $\mu_{FE}$ (note that until now, only this value was presented, with the peak located around $V_{GS} = 25 - 30$ V) but rather $\mu_{FE}$ for a smaller $V_{GS}$, e.g., 15 V, where $R_C$ is higher, the order presented for $\mu_{FE}$ is still preserved since $r_{ch}$ continues to be much higher than $R_C$.

For $L = 5 \mu$m, $R_C$ is comparable to or even higher than $r_{ch} \times L$ throughout the $V_{GS}$ range; thus, both $R_C$ and $r_{ch} \times L$ are significant to $R_T$. For $V_{GS} = 30$ V, the $\mu_{FE}$ order for the different materials previously listed remains essentially the same. However, for $\mu_{FE}$ determined at $V_{GS} = 15$ V, the situation is quite different since $R_C$ is dominant in $R_T$ for all the materials except Ti. Thus, in this case, $\mu_{FE}$ increases in another order, i.e., Ti/Au, IZO, Mo, and Ti.

Taking into account the aforementioned conditions, we can now go back to Fig. 5 and plot the evolution of $\mu_{FE}$ with $L$ at $V_{GS} = 15$ V. The results show, as expected, only a very small variation of $\mu_{FE}$ with $L$ for Ti, whereas for Ti/Au, a clear increase of $\mu_{FE}$ with $L$ is observed. This reinforces the idea that $R_C$ has a strong effect on the electrical properties of the TFTs.

Finally, it remains unclear what happens when Al is used for the source/drain electrode. In this case, we always noticed severe current crowding in the output characteristics at low $V_{DS}$, which is independent of when the annealing treatment is performed (before or after depositing the electrodes). Thus, it seems that a considerable barrier is formed between Al and GIZO, which makes it impossible to do any reliable characterization in the linear regime.
IV. CONCLUSION

The role of the contact resistance was analyzed in GIZO-based TFTs with different source/drain electrodes. The influence of the annealing step, before or after the deposition of source/drain electrodes, was studied and led to the conclusion that devices with improved electrical properties are generally obtained for the last case. Concerning the different source/drain materials, Ti/Au led to the highest $\mu_{FE}$, whereas $V_T$ and on/off ratio were similar for all the tested materials. Evolution of $\mu_{FE}$ and $V_T$ with $L$ revealed no significant variation of $V_T$, but a pronounced decrease of $\mu_{FE}$ for lower $L$ was observed, which was ascribed to the higher relative influence of the contact resistance on the total resistance of short-channel devices. For high $V_{GS}$, when $R_C$ started to saturate at a minimum value, $R_C$ was found to be in the range of 10 (Ti) to 20 (Ti/Au) kΩ, with these values around one order of magnitude lower than the 100 kΩ presented by Jackson et al. for ZTO-based TFTs with Al contacts. A more detailed analysis of the contact resistance issues and their role in all device performances is underway by the present working team, which aims to improve the overall device performance, including the transport mechanism that takes place between the source/drain and the channel region.

ACKNOWLEDGMENT

The authors would like to thank R. Perez from the Nanotechnology Platform, Barcelona Scientific Park, for the TOF-SIMS measurements.

REFERENCES


Joan R. Morante was born in Mataró, Spain. He received the Ph.D. degree in physics from the University of Barcelona, Barcelona, Spain, in 1980. Since 1985, he has been a Professor of electronics and the Director of the research group Electronic Materials and Engineering (EME; currently the Department of Electronics). He is currently the Director of the consolidated research group EME, the Co-Director of the Center of Microsystems of the Technological Innovation Network of the Generalitat of Catalonia (CEMIC), and the Director of the Reference Center in Advanced Materials for Energy of the Generalitat of Catalonia (CrRMAE). His activities have been centered in electronic materials and devices and the assessment of their related technologies and processes, particularly emphasizing on semiconductor materials technology transfer, electronic ceramics, metallic oxides, and sensing materials. Likewise, he has a particular interest in nanosciences, being the Coordinator in the energy work group of IN2UB, as well as in micro- and nanotechnologies, where he has specialized in the development of microsystems and integrated chemical sensors based on nanostructures and their functionalization. He has taken part in many R&D international projects in the programs BRIFE, Growth, priority 3 in 6FP, ESPRIT, IST, priority 2 in 6FP, JOULE, Energy, and industrial projects in programs EUREKA, IBEROEKA y CRAFT, as well as in private industrial projects. He has authored or coauthored more than 400 papers published in international journals and conference proceedings and has directed more than 25 doctoral theses. He is the holder of several patents.

Prof. Morante is a member of international committees and editorial teams of journals and has been a Guest Editor of many special issues. He has been awarded the Narcís Monturiol of the Generalitat of Catalonia and the Senior Research Distinction Award from the Generalitat of Catalonia.
Elvira Fortunato was born in 1964. She received the Ph.D. degree in physics and materials and the Aggregation (teaching certificate) in microelectronic and optoelectronic from the New University of Lisbon, Caparica, Portugal, in 1995 and 2005, respectively. She has been an Associate Professor with the Materials Science Department, New University of Lisbon, since 1998, the Director of the Materials Research Center (CENIMAT) since 1998, and the Director of the Institute of Nanotechnologies, Nanomaterials and Nanosciences (I3N) since 2007. She has pioneered European research on thin-film transistors based on oxide semiconductors, demonstrating that oxide materials may be used as true semiconductors. Her recent accomplishments include the first ZnO-based transparent thin-film transistor (TTFT) deposited at room temperature by RF magnetron sputtering with a high field-effect mobility. Her current interests are in the design, fabrication, conduction transport mechanisms, and characterization of amorphous multicomponent oxide-based TTFTs. She is also interested in the development of novel electrochromic devices. She published (or has in press) more than 240 scientific papers and supervised (or has supervised) five postdoctoral and 16 Ph.D./M.Sc. students.

Prof. Fortunato has been an Associate Editor of *Physica Status Solidi (Rapid Research Letters)* since November 2006 (Wiley). She was the recipient of the Scientific Excellence Award from the Portuguese Science Foundation (FCT-MCTES) in 2005 and the Gold Medal Award from the Municipality of Almada in 2007.